

RJL5014DPP

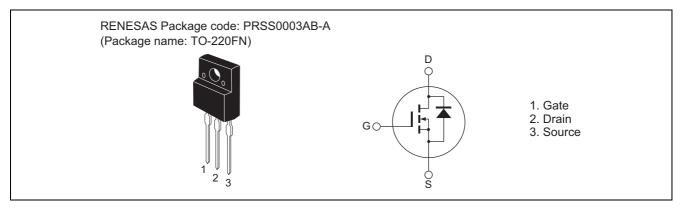
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1690-0300 Rev.3.00 Jun 13, 2008

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D ^{Note4}	19	А
Drain peak current	Note1	57	А
Body-drain diode reverse drain current	I _{DR}	19	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	57	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.88	mJ
Channel dissipation	Pch Note2	35	W
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

- 2. Value at Tc = 25° C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

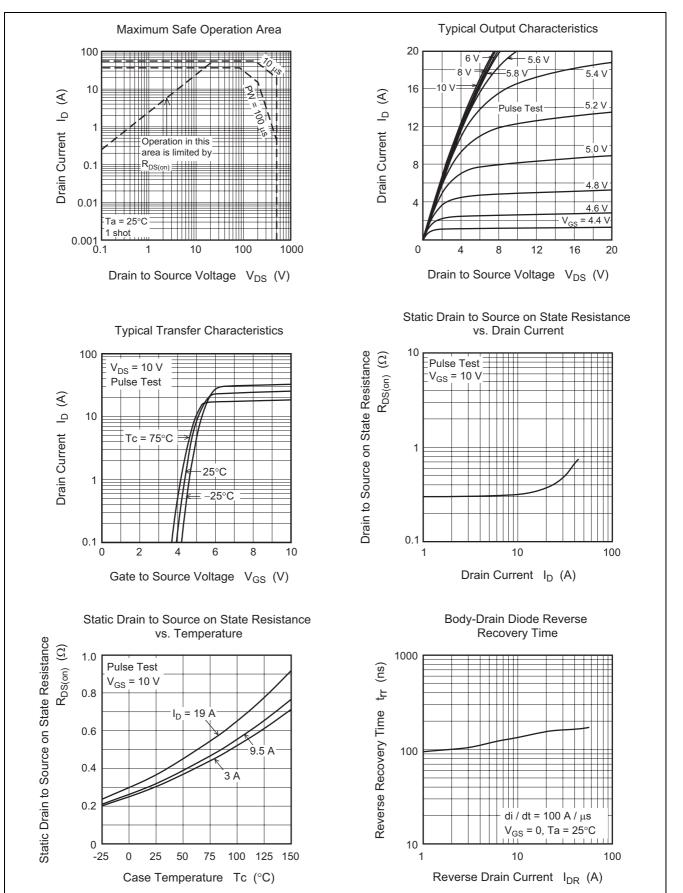
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Electrical Characteristics

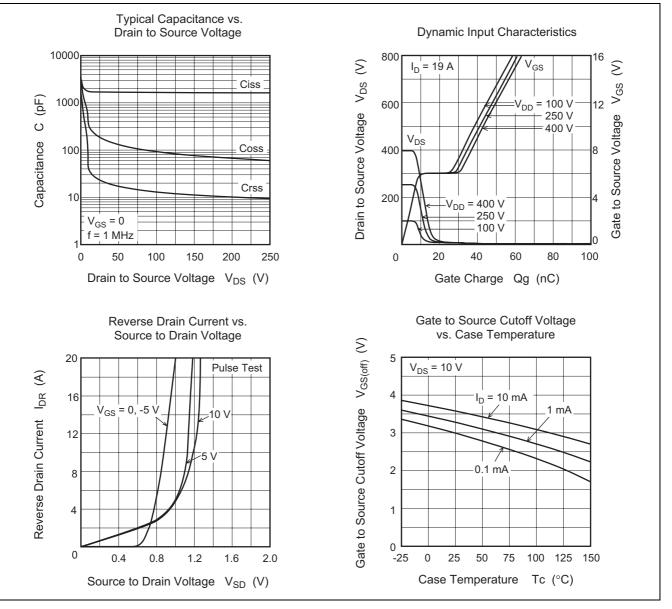
						(Ta = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}		—	10	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$		0.32	0.40	Ω	$I_D = 9.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
Input capacitance	Ciss	_	1700	—	pF	$V_{DS} = 25 V$ $V_{GS} = 0$ $f = 1 MHz$
Output capacitance	Coss	_	190	—	pF	
Reverse transfer capacitance	Crss		23	_	pF	
Turn-on delay time	t _{d(on)}	_	32	_	ns	$I_{D} = 9.5 \text{ A} \\ V_{GS} = 10 \text{ V} \\ R_{L} = 26.3 \Omega \\ Rg = 10 \Omega$
Rise time	tr	-	27	—	ns	
Turn-off delay time	t _{d(off)}	-	95	—	ns	
Fall time	t _f		20	—	ns	
Total gate charge	Qg		43	—	nC	V _{DD} = 400 V
Gate to source charge	Qgs	-	8.2	—	nC	V _{GS} = 10 V I _D = 19 A
Gate to drain charge	Qgd	_	21.8	_	nC	
Body-drain diode forward voltage	V _{DF}	_	1.00	1.65	V	$I_F = 19 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}		160	_	ns	$I_F = 19 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

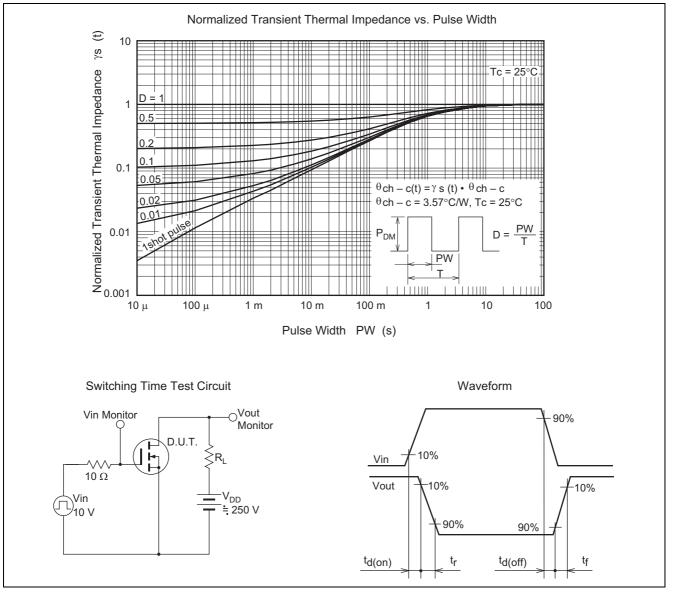
Notes: 5. Pulse test

Main Characteristics

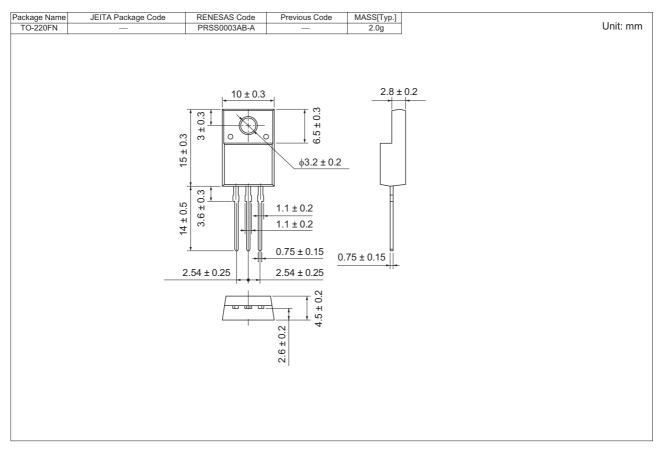


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJL5014DPP-00-T2	1050 pcs	Box (Tube)

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